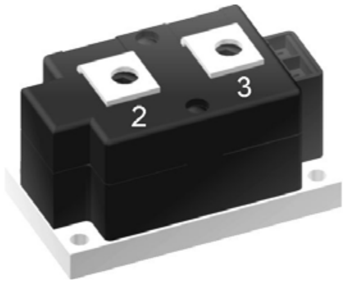
Standard Rectifier Module

V_{RRM}	=	1600 V
I_{FAV}	=	608 A
V_F	=	1.01 V

Single Diode

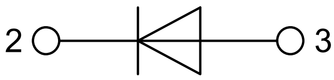
Part number

MDO600-16N1



Backside: isolated

E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

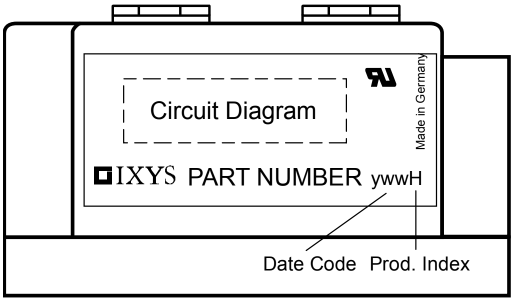
- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1700	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1600	V
I_R	*reverse current*	V_R = 1600 V	T_{VJ} = 25°C			1	mA
		V_R = 1600 V	T_{VJ} = 140°C			30	mA
V_F	*forward voltage drop*	I_F = 600 A	T_{VJ} = 25°C			1.12	V
		I_F = 1200 A				1.30	V
		I_F = 600 A	T_{VJ} = 125 °C			1.01	V
		I_F = 1200 A				1.23	V
I_{FAV}	*average forward current*	T_C = 85°C	T_{VJ} = 140°C			608	A
		180° sine d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 140°C			0.76	V
r_F	*slope resistance*					0.32	mΩ
R_{thJC}	*thermal resistance junction to case*					0.072	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.024		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			1600	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			15.0	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			16.2	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 140°C			12.8	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			13.8	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.13	MA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.09	MA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 140°C			812.8	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			788.8	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		762		pF

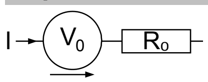
Package Y1				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal				600	A
T_{VJ}	*virtual junction temperature*			-40		140	°C
T_{op}	*operation temperature*			-40		125	°C
T_{stg}	*storage temperature*			-40		125	°C
Weight					650		g
M_D	*mounting torque*			4.5		7	Nm
M_T	*terminal torque*			11		13	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	16.0			mm
$d_{Spb/Apb}$			*terminal to backside*	25.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \le 1$ mA	3600			V
		t = 1 minute		3000			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDO600-16N1	MDO600-16N1	Box	3	509707

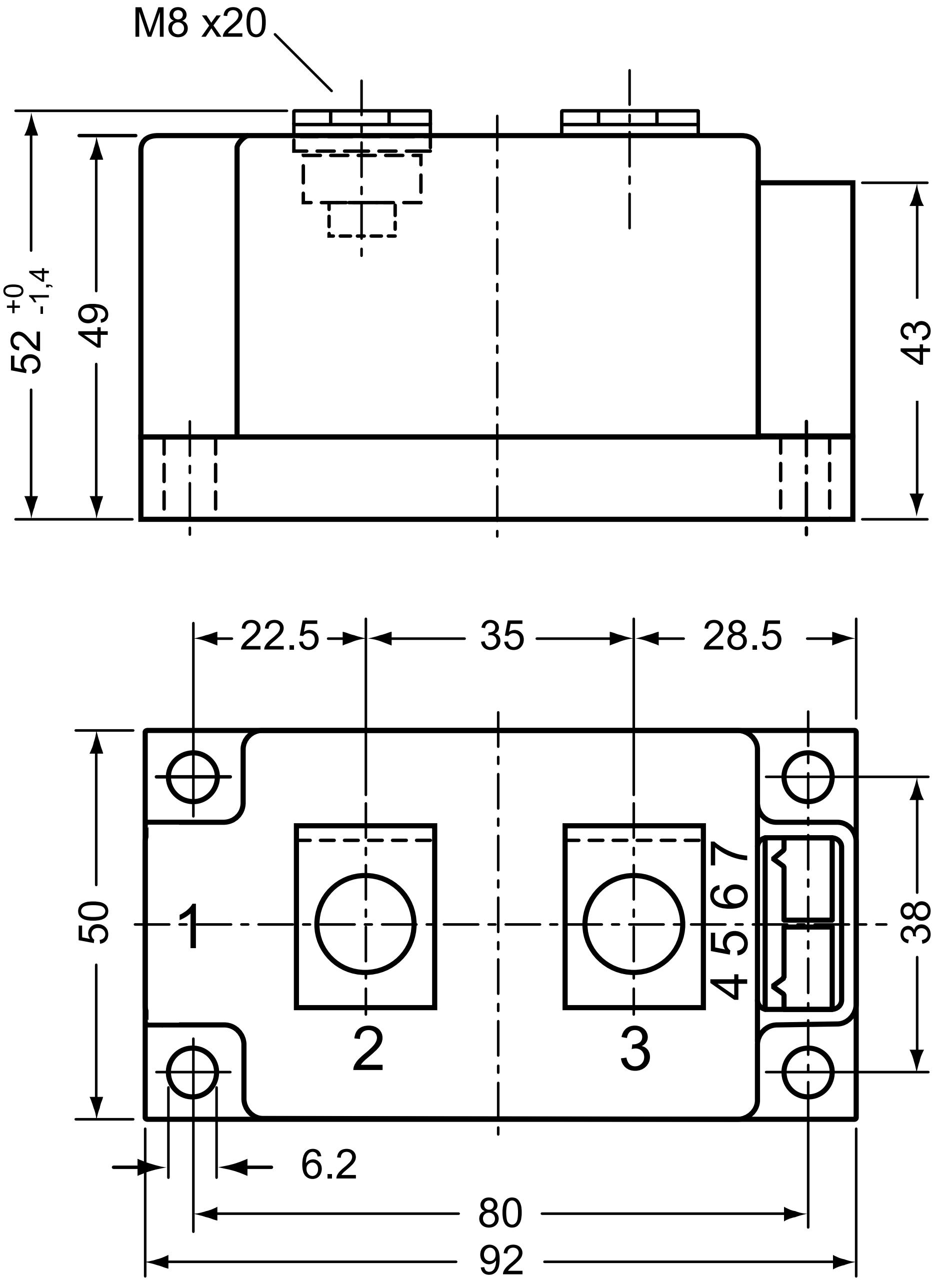
Equivalent Circuits for Simulation

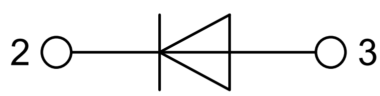
** on die level* $T_{VJ} = 140\,°C$



		Rectifier	
$V_{0\,max}$	*threshold voltage*	0.76	V
$R_{0\,max}$	*slope resistance **	0.13	mΩ

Outlines Y1





Rectifier

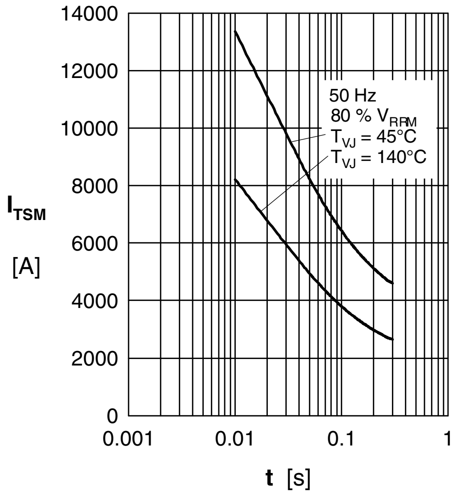


Fig. 1 Surge overload current
I_{FSM}: Crest value, t: duration

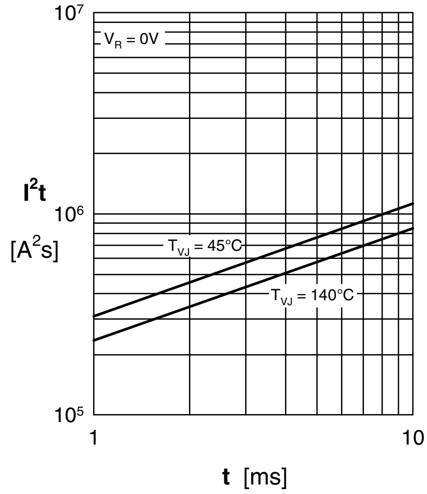


Fig. 2 I^2t versus time (1-10 ms)

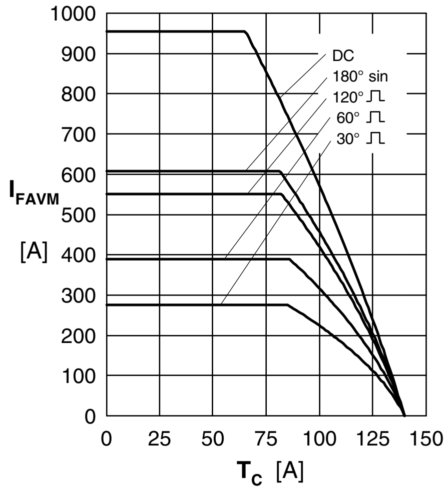


Fig. 3 Max. forward current
at case temperature

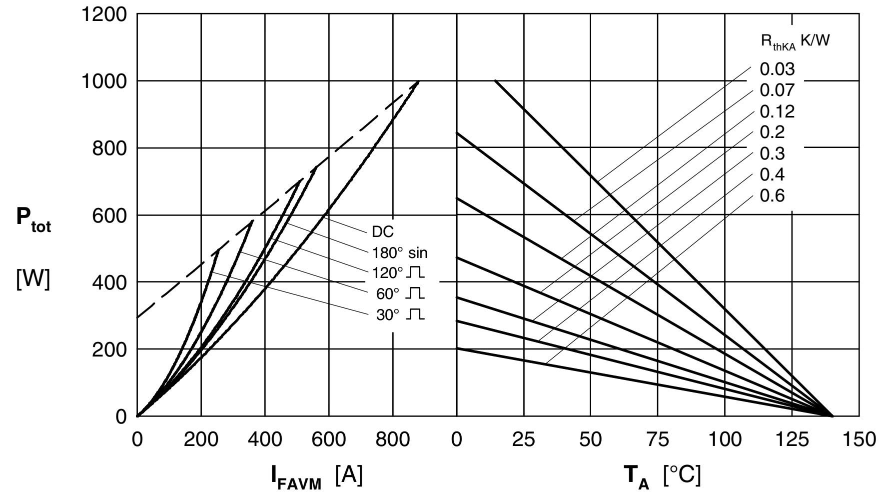


Fig. 4 Power dissipation vs. forward current and ambient temperature

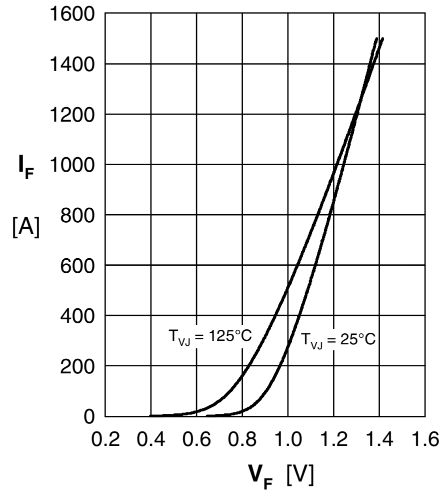


Fig. 5 Forward current I_F vs. V_F

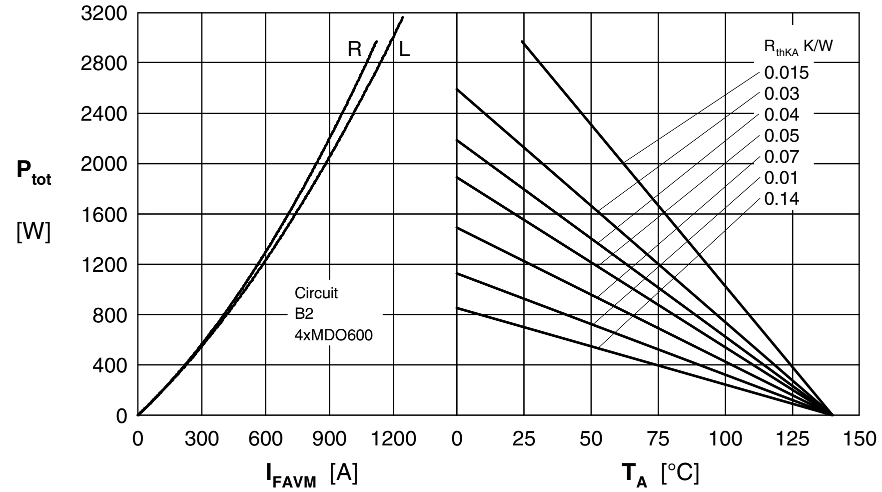


Fig. 6 Single phase rectifier bridge: Power dissipation vs. direct output current
and ambient temperature R = resistive load, L = inductive load

Rectifier

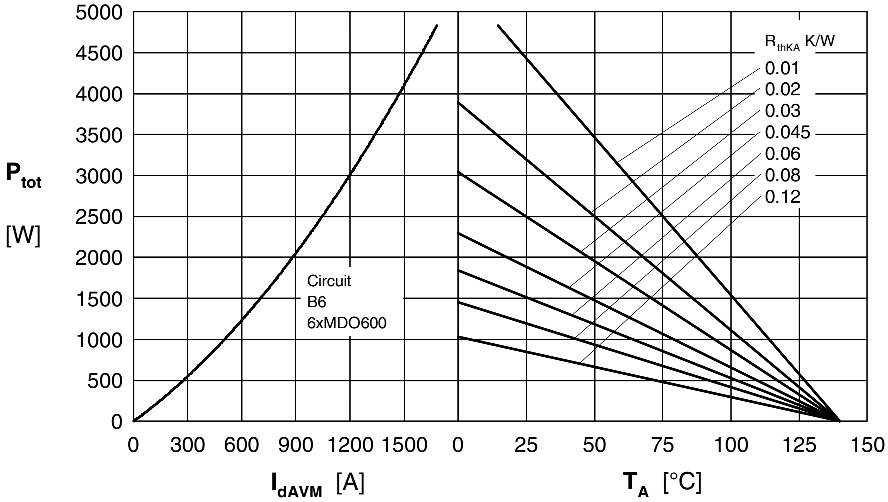


Fig. 7 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

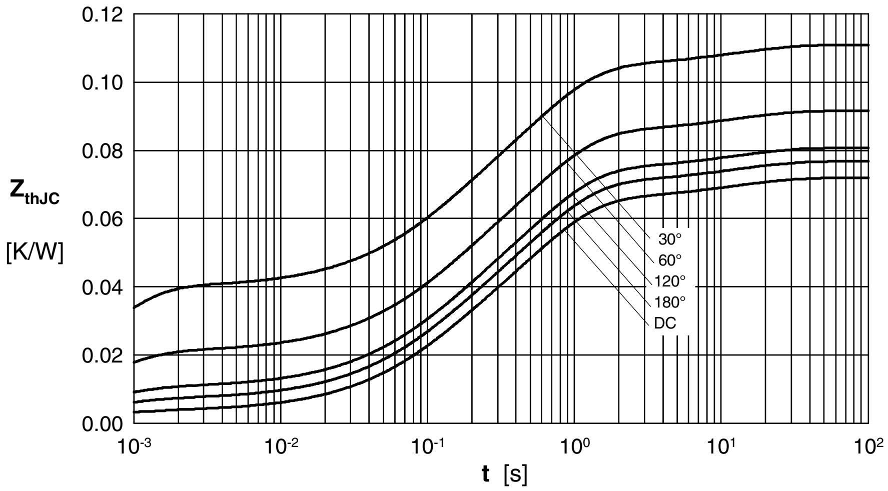


Fig. 8 Transient thermal impedance junction to case

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.072
180°	0.0768
120°	0.081
60°	0.092
30°	0.111

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12

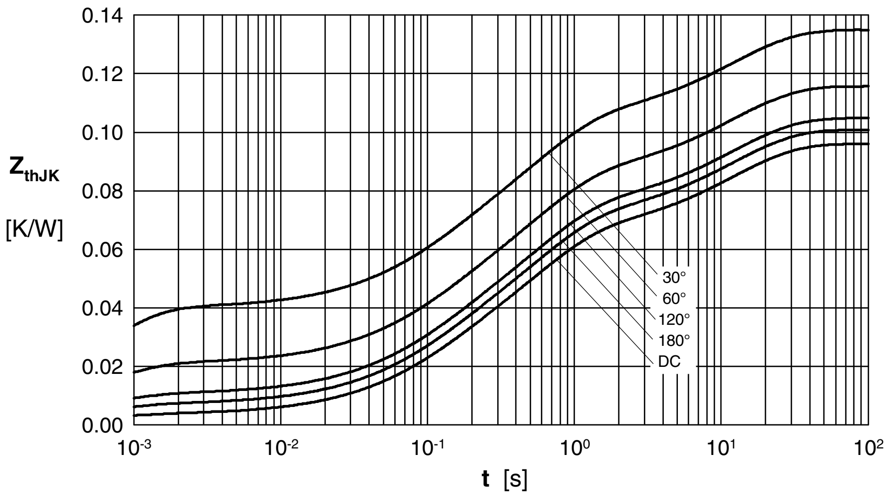


Fig. 9 Transient thermal impedance junction to heatsink

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.096
180°C	0.1
120°C	0.105
60°C	0.116
30°C	0.135

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.067	12
5	0.024	12